**Product data sheet** 

# 1. General description

Planar passivated high commutation three quadrant triac in a SOT54 (TO-92) plastic package. This "series B" triac is designed to commutate the full RMS current at the maximum junction temperature without the aid of a snubber.

### 2. Features and benefits

- 3Q technology for improved noise immunity
- · High commutation capability with maximum false trigger immunity
- High voltage capability
- Less sensitive gate for highest noise immunity
- · Planar passivated for voltage ruggedness and reliability
- · Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt

## 3. Applications

- · General purpose motor control
- · Small loads in washing machines
- Solenoid drivers

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Mir	ո  Тур	Max	Unit
$V_{DRM}$	repetitive peak off- state voltage		-	-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>lead</sub> ≤ 54 °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	-	1	Α
Static characte	eristics					
Іст	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	5	-	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G -;$ $T_j = 25 ^{\circ}\text{C; } \underline{\text{Fig. 7}}$	5	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G-;$ $T_j = 25 \text{ °C}; Fig. 7$	5	-	50	mA

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# **5. Pinning information**

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		T2——T1
2	G	gate		sym051
3	T1	main terminal 1	TO-92 (SOT54)	symoon

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
BTA201-800B	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54		

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# 7. Limiting values

### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>lead</sub> ≤ 54 °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	1	Α
I <sub>TSM</sub>	non-repetitive peak on-	full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 16.8 ms	-	13.7	Α
	state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig. 4; Fig. 5	-	12.5	Α
I <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	0.78	A²s
dl <sub>T</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 0.2 A	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
P <sub>GM</sub>	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.1	W
Tj	junction temperature		-40	125	°C

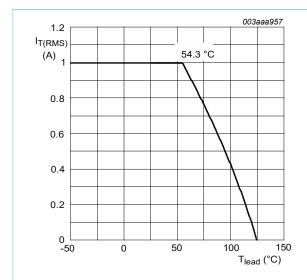


Fig. 1. RMS on-state current as a function of lead temperature; maximum values

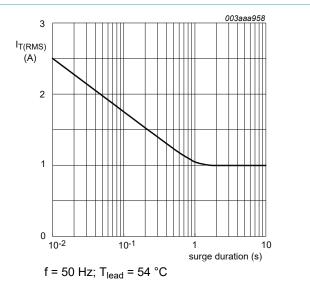


Fig. 2. RMS on-state current as a function of surge duration; maximum values

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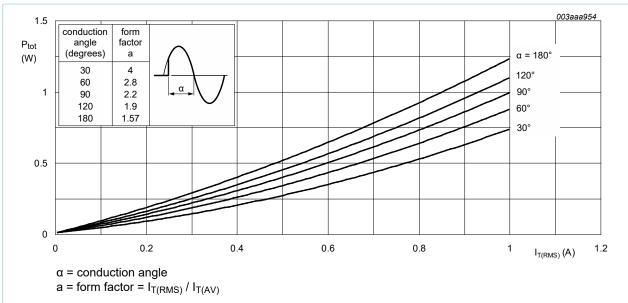


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

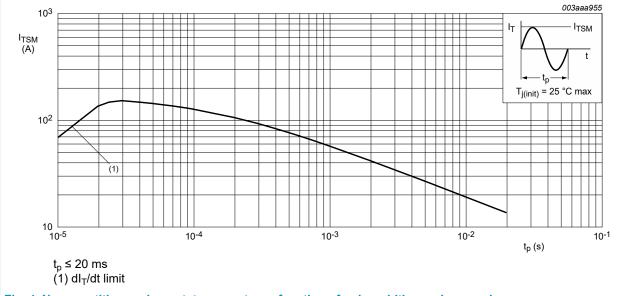


Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

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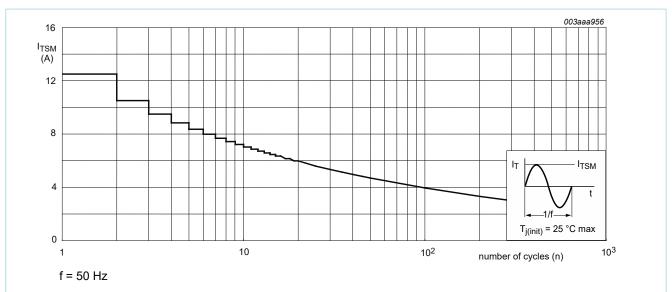


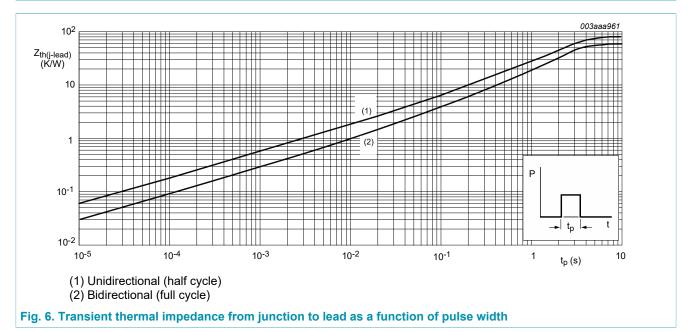
Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-lead)</sub>	thermal resistance from junction to lead	full cycle; Fig. 6	-	-	60	K/W
		half cycle; Fig. 6	-	-	80	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board mounted; lead length = 4 mm	-	150	-	K/W



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## 9. Characteristics

#### **Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					,
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; } Fig. 7$	5	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$	5	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	5	-	50	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	50	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	-	30	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	30	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.2	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; Fig. 11	0.2	0.3	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic cl	haracteristics		'			
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit; Fig. 12	1000	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 1 A; $dV_{com}/dt$ = 20 V/s; (snubberless condition); gate open circuit	12	-	-	A/ms
		$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 1 A; $dV_{com}/dt$ = 10 V/µs; gate open circuit	16	-	-	A/ms

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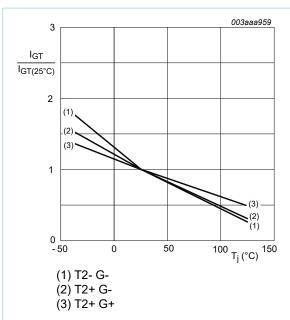


Fig. 7. Normalized gate trigger current as a function of junction temperature

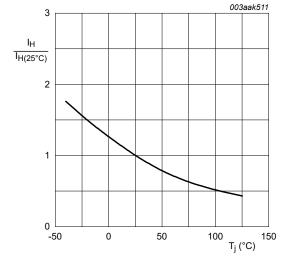


Fig. 9. Normalized holding current as a function of junction temperature

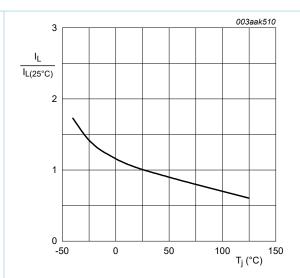
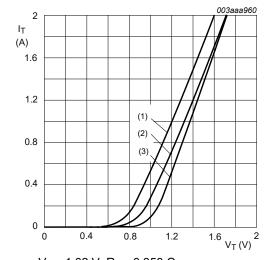


Fig. 8. Normalized latching current as a function of junction temperature



 $\begin{array}{l} \text{V}_{\text{o}} = 1.02 \text{ V}; \text{ R}_{\text{s}} = 0.358 \ \Omega \\ \text{(1)} \text{ T}_{\text{j}} = 125 \ ^{\circ}\text{C}; \text{ typical values} \\ \text{(2)} \text{ T}_{\text{j}} = 125 \ ^{\circ}\text{C}; \text{ maximum values} \\ \text{(3)} \text{ T}_{\text{j}} = 25 \ ^{\circ}\text{C}; \text{ maximum values} \end{array}$ 

Fig. 10. On-state current as a function of on-state voltage

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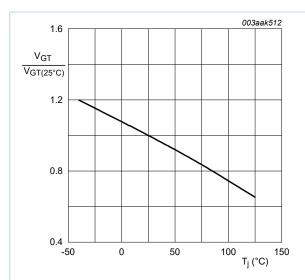


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

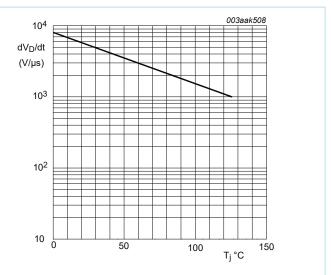
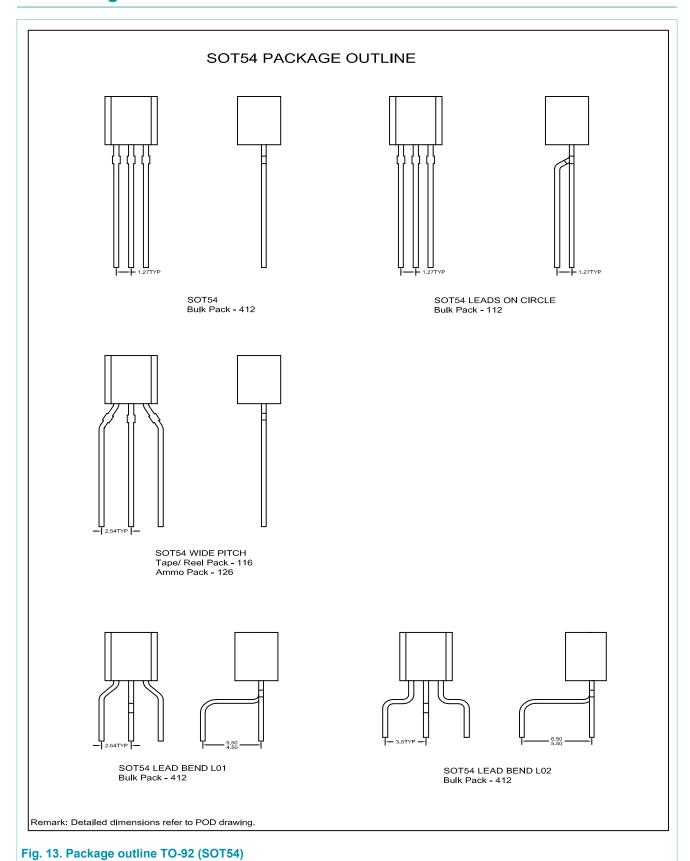


Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; minimum values

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# 10. Package outline



DTA204 000D

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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